

IPZ65R019C7XKSA1

IPZ65R019C7XKSA1 Information

Heisener.com

Part Number IPZ65R019C7XKSA1 **Manufacturer** Infineon Technologies

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 650V TO247-4

Package TO-247-4

For the pricing/inventory/lead time, please contact

us

For Reference Only

Website: https://www.heisener.com

E-mail: salesdept@heisener.com



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Certified Quality

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IPZ65R019C7XKSA1 Specifications

Manufacturer Part Number IPZ65R019C7XKSA1 Manufacturer Infineon Technologies Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-247-4 Series CoolMOS? C7 FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 650V Current - Continuous Drain (Id) @ 25°C 75A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 2.92mA Gate Charge (Qg) (Max) @ Vgs 215nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 9900pF @ 400V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 446W (Tc) Rds On (Max) @ Id, Vgs 19 mOhm @ 58.3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package PG-T0247-4 Package / Case TO-247-4 Report errors?		
Category Discrete Semiconductor Products Package TO-247-4 Series CoolMOS? C7 FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 650V Current - Continuous Drain (Id) @ 25°C 75A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 2.92mA Gate Charge (Qg) (Max) @ Vgs 215nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 9900pF @ 400V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 446W (Tc) Rds On (Max) @ Id, Vgs 19 mOhm @ 58.3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO247-4 Package / Case TO-247-4	Manufacturer Part Number	IPZ65R019C7XKSA1
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SeriesCoolMOS? C7FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)650VCurrent - Continuous Drain (Id) @ 25°C75A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 2.92mAGate Charge (Qg) (Max) @ Vgs215nC @ 10VInput Capacitance (Ciss) (Max) @ Vds9900pF @ 400VVgs (Max)±20VFET Feature-Power Dissipation (Max)446W (Tc)Rds On (Max) @ Id, Vgs19 mOhm @ 58.3A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO247-4Package / CaseTO-247-4		Transistors - FETs, MOSFETs - Single
FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 75A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 2.92mA Gate Charge (Qg) (Max) @ Vgs 215nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 9900pF @ 400V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 446W (Tc) Rds On (Max) @ Id, Vgs 19 mOhm @ 58.3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO247-4 Package / Case	Package	TO-247-4
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 75A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package PG-TO247-4 Package / Case MOSFET (Metal Oxide) 650V 75A (Tc) 75A (Tc	Series	CoolMOS? C7
Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 75A (Tc) 75A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 4V @ 2.92mA Gate Charge (Qg) (Max) @ Vgs 1nput Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 19 mOhm @ 58.3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Supplier Device Package PG-TO247-4 Package / Case 75A (Tc) 75D (P 10V 10V 10V 10V 440V 10V 10V 10V	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 19 mOhm @ 58.3A, 10V Operating Temperature Supplier Device Package PG-TO247-4 Package / Case 75A (Tc) 75A (Tc	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 4V @ 2.92mA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 19 mOhm @ 58.3A, 10V Operating Temperature Supplier Device Package PG-TO247-4 Package / Case 10V 4V @ 2.92mA 40V 40V FET Ge 10V Fe 400V FET Feature	Drain to Source Voltage (Vdss)	650V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package PG-TO247-4 Package / Case 4V @ 2.92mA 4V @ 2.92mA 215nC @ 10V 215nC @ 10V 400V 440W 400V 440W 400V 446W (Tc) 19 mOhm @ 58.3A, 10V 755°C ~ 150°C (TJ) Through Hole Supplier Device Package PG-TO247-4 TO-247-4	Current - Continuous Drain (Id) @ 25°C	75A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 9900pF @ 400V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 19 mOhm @ 58.3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO247-4 Package / Case 70-247-4	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 19 mOhm @ 58.3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO247-4 Package / Case TO-247-4	Vgs(th) (Max) @ Id	4V @ 2.92mA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)446W (Tc)Rds On (Max) @ Id, Vgs19 mOhm @ 58.3A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO247-4Package / CaseTO-247-4	Gate Charge (Qg) (Max) @ Vgs	215nC @ 10V
FET Feature - Power Dissipation (Max) 446W (Tc) Rds On (Max) @ Id, Vgs 19 mOhm @ 58.3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO247-4 Package / Case TO-247-4	Input Capacitance (Ciss) (Max) @ Vds	9900pF @ 400V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 19 mOhm @ 58.3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO247-4 Package / Case TO-247-4	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs 19 mOhm @ 58.3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO247-4 Package / Case TO-247-4	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO247-4 Package / Case TO-247-4	Power Dissipation (Max)	446W (Tc)
Mounting Type Through Hole Supplier Device Package PG-TO247-4 Package / Case TO-247-4	Rds On (Max) @ Id, Vgs	19 mOhm @ 58.3A, 10V
Supplier Device Package PG-TO247-4 Package / Case TO-247-4	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-247-4	Mounting Type	Through Hole
	Supplier Device Package	PG-TO247-4
Report errors?	Package / Case	TO-247-4
		Report errors?

IPZ65R019C7XKSA1 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IPZ65R019C7XKSA1 Payment Methods



















IPZ65R019C7XKSA1 Shipping Methods













If you have any question about IPZ65R019C7XKSA1, please do not hesitate to contact us!

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